

**PNP Silicon Digital Transistor**

- Built in bias resistor ( $R_1 = 2.2\text{ k}\Omega$ ,  $R_2 = 10\text{ k}\Omega$ )
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



| Type   | Marking | Pin Configuration |     |     | Package |
|--------|---------|-------------------|-----|-----|---------|
|        |         | 1=B               | 2=E | 3=C |         |
| BCR555 | XD5     | 1=B               | 2=E | 3=C | SOT23   |

**Maximum Ratings**

| Parameter   | Symbol       | Value       | Unit             |
|---|--------------|-------------|------------------|
| Collector-emitter voltage                                       | $V_{CEO}$    | 50          | V                |
| Collector-base voltage  | $V_{CBO}$    | 50          |                  |
| Input forward voltage   | $V_{i(fwd)}$ | 20          |                  |
| Input reverse voltage   | $V_{i(rev)}$ | 5           |                  |
| Collector current   | $I_C$        | 500         | mA               |
| Total power dissipation-<br>$T_S \leq 79\text{ }^\circ\text{C}$ | $P_{tot}$    | 330         | mW               |
| Junction temperature  | $T_j$        | 150         | $^\circ\text{C}$ |
| Storage temperature   | $T_{stg}$    | -65 ... 150 |                  |

**Thermal Resistance**

| Parameter                                | Symbol     | Value      | Unit |
|--|------------|------------|------|
| Junction - soldering point <sup>1)</sup> | $R_{thJS}$ | $\leq 215$ | K/W  |

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

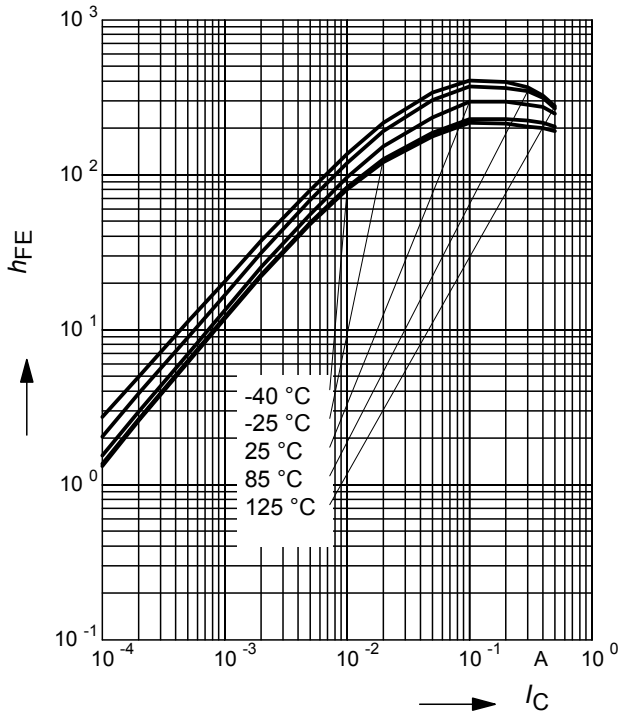
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

| Parameter   | Symbol        | Values |      |      | Unit       |
|---|---------------|--------|------|------|------------|
|   |               | min.   | typ. | max. |            |
| <b>DC Characteristics</b>   |               |        |      |      |            |
| Collector-emitter breakdown voltage<br>$I_C = 100 \mu\text{A}, I_B = 0$                           | $V_{(BR)CEO}$ | 50     | -    | -    | V          |
| Collector-base breakdown voltage<br>$I_C = 10 \mu\text{A}, I_E = 0$                               | $V_{(BR)CBO}$ | 50     | -    | -    |            |
| Collector-base cutoff current<br>$V_{CB} = 50 \text{ V}, I_E = 0$                                 | $I_{CBO}$     | -      | -    | 100  | nA         |
| Emitter-base cutoff current<br>$V_{EB} = 5 \text{ V}, I_C = 0$                                    | $I_{EBO}$     | -      | -    | 0.65 | mA         |
| DC current gain-<br>$I_C = 50 \text{ mA}, V_{CE} = 5 \text{ V}$                                   | $h_{FE}$      | 70     | -    | -    | -          |
| Collector-emitter saturation voltage <sup>1)</sup><br>$I_C = 50 \text{ mA}, I_B = 2.5 \text{ mA}$ | $V_{CEsat}$   | -      | -    | 0.3  | V          |
| Input off voltage<br>$I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$                                | $V_{i(off)}$  | 0.4    | -    | 1    |            |
| Input on voltage<br>$I_C = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$                                 | $V_{i(on)}$   | 0.5    | -    | 1.4  |            |
| Input resistor  | $R_1$         | 1.5    | 2.2  | 2.9  | k $\Omega$ |
| Resistor ratio  | $R_1/R_2$     | 0.19   | 0.22 | 0.24 | -          |
| <b>AC Characteristics</b>   |               |        |      |      |            |
| Transition frequency<br>$I_C = 50 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$          | $f_T$         | -      | 150  | -    | MHz        |

<sup>1</sup>Pulse test:  $t < 300 \mu\text{s}$ ;  $D < 2\%$

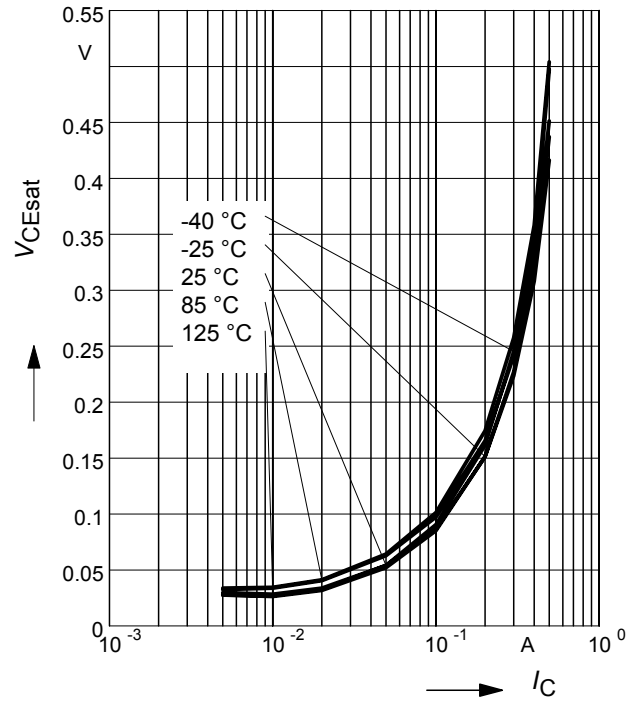
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5\text{ V}$  (common emitter configuration)



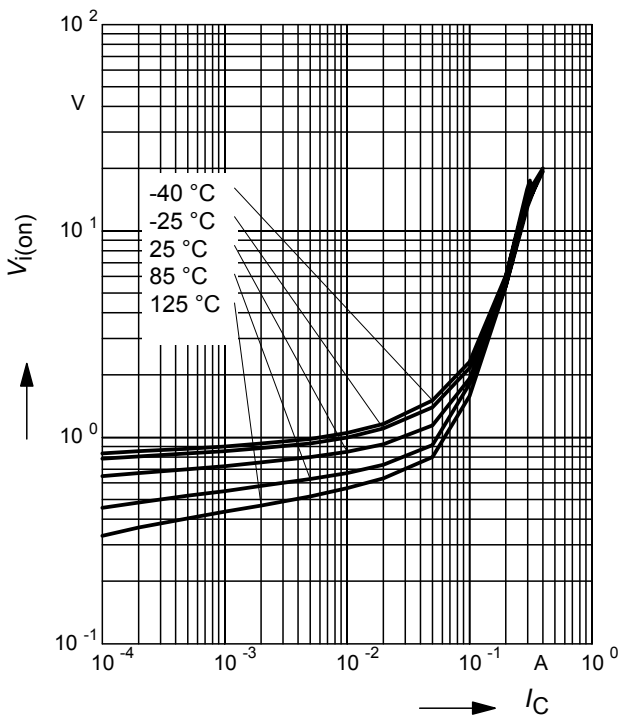
**Collector-emitter saturation voltage**

$V_{CEsat} = f(I_C), I_C/I_B = 20$



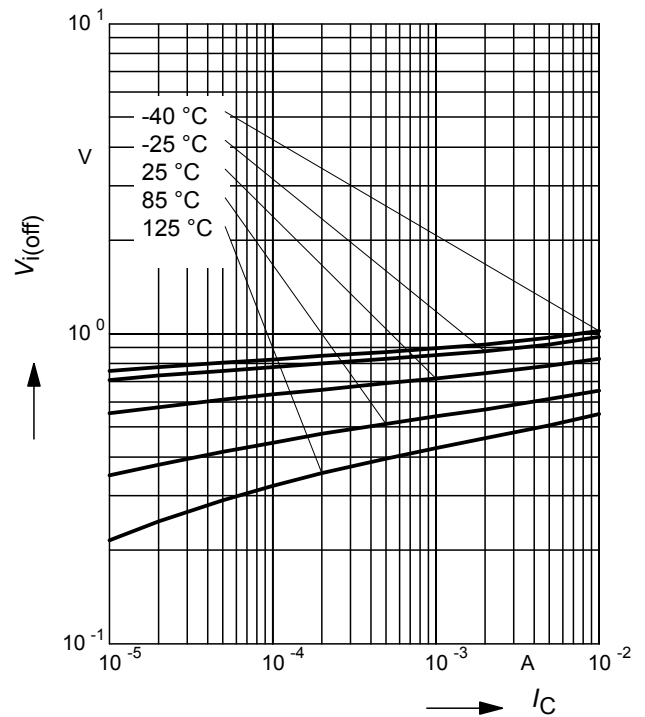
**Input on Voltage  $V_{i(on)} = f(I_C)$**

$V_{CE} = 0.3\text{ V}$  (common emitter configuration)



**Input off voltage  $V_{i(off)} = f(I_C)$**

$V_{CE} = 5\text{ V}$  (common emitter configuration)



**Total power dissipation  $P_{tot} = f(T_S)$**



**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$



Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print

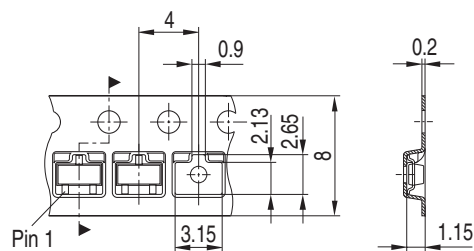


Marking Layout (Example)



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel



**Edition 2009-11-16**

**Published by  
Infineon Technologies AG  
81726 Munich, Germany**

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